

## IGBT MODULE ( N series )

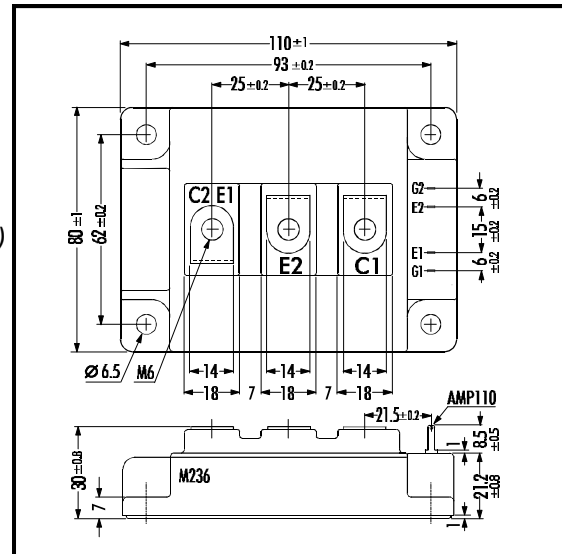
### ■ Features

- Square RBSOA
- Low Saturation Voltage
- Less Total Power Dissipation
- Improved FWD Characteristic
- Minimized Internal Stray Inductance
- Overcurrent Limiting Function (~3 Times Rated Current)

### ■ Applications

- High Power Switching
- A.C. Motor Controls
- D.C. Motor Controls
- Uninterruptible Power Supply

## ■ Outline Drawing



## ■ Maximum Ratings and Characteristics

### • Absolute Maximum Ratings ( T<sub>c</sub>=25°C )

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V <sub>CEs</sub>	600	V
Gate -Emitter Voltage	V <sub>GES</sub>	± 20	V
Collector Current	Continuous	I <sub>C</sub>	600
	1ms	I <sub>C PULSE</sub>	1200
	Continuous	-I <sub>C</sub>	600
	1ms	-I <sub>C PULSE</sub>	1200
Max. Power Dissipation	P <sub>C</sub>	2100	W
Operating Temperature	T <sub>j</sub>	+150	°C
Storage Temperature	T <sub>stg</sub>	-40 ~ +125	°C
Isolation Voltage	A.C. 1min.	V <sub>is</sub>	2500
Screw Torque	Mounting *1	3.5	Nm
	Terminals *2	4.5	

Note: \*1:Recommendable Value; 2.5 ~ 3.5 Nm (M5) or (M6)  
\*2:Recommendable Value; 3.5 ~ 4.5 Nm (M6)

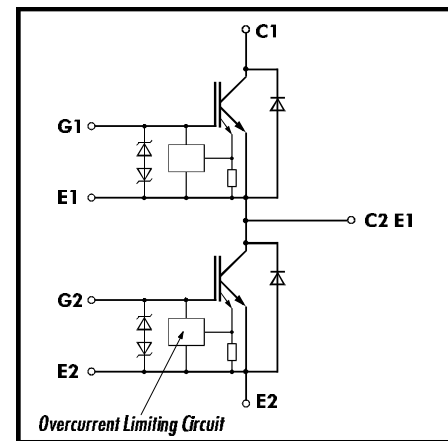
### • Electrical Characteristics ( at T<sub>j</sub>=25°C )

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I <sub>CEs</sub>	V <sub>GE</sub> =0V V <sub>CE</sub> =600V			4.0	mA
Gate-Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V V <sub>GE</sub> =± 20V			60	μA
Gate-Emitter Threshold Voltage	V <sub>GE(th)</sub>	V <sub>GE</sub> =20V I <sub>C</sub> =600mA	4.5		7.5	V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	V <sub>GE</sub> =15V I <sub>C</sub> =600A			2.9	V
Input capacitance	C <sub>ies</sub>	V <sub>GE</sub> =0V		39600		pF
Output capacitance	C <sub>oes</sub>	V <sub>CE</sub> =10V		8800		
Reverse Transfer capacitance	C <sub>res</sub>	f=1MHz		2670		
Turn-on Time	t <sub>ON</sub>	V <sub>CC</sub> =300V		0.6	1.2	μs
	t <sub>r</sub>	I <sub>C</sub> =600A		0.2	0.6	
Turn-off Time	t <sub>OFF</sub>	V <sub>GE</sub> =± 15V		0.6	1.0	
	t <sub>f</sub>	R <sub>G</sub> =2.7Ω		0.2	0.35	
Diode Forward On-Voltage	V <sub>F</sub>	I <sub>F</sub> =600A V <sub>GE</sub> =0V			3.1	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =600A			300	ns

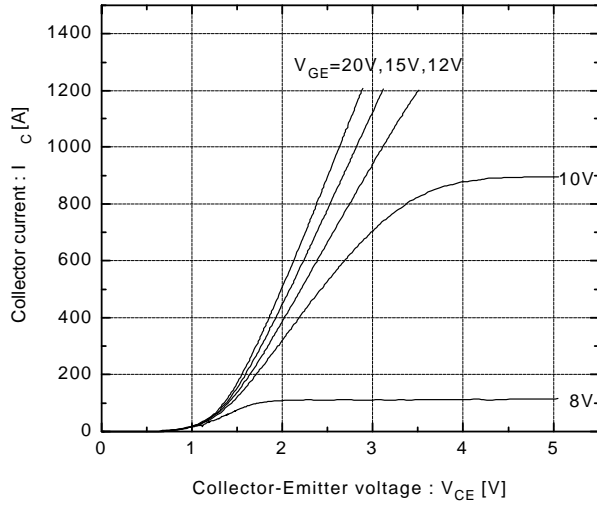
### • Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R <sub>th(j-c)</sub>	IGBT			0.06	°C/W
	R <sub>th(f-c)</sub>	Diode			0.15	
	R <sub>th(c-t)</sub>	With Thermal Compound		0.0167		

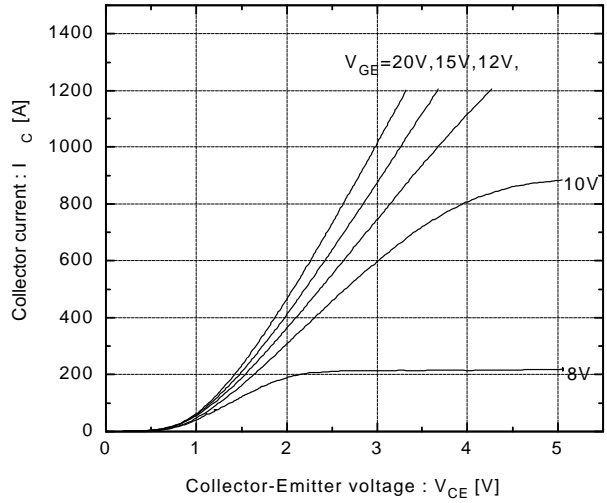
## ■ Equivalent Circuit



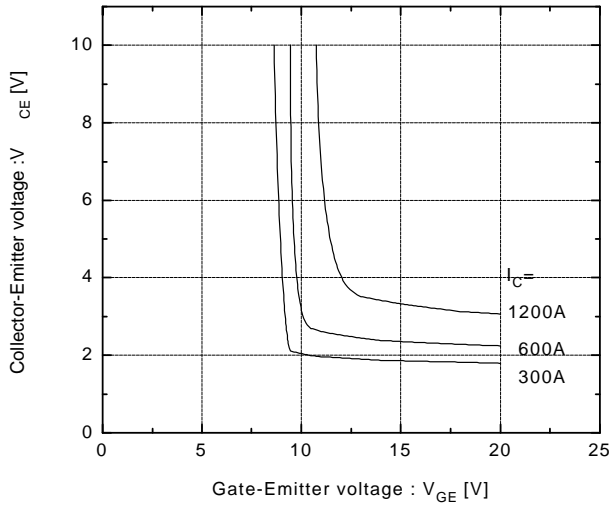
Collector current vs. Collector-Emittor voltage  
 $T_j=25^\circ\text{C}$



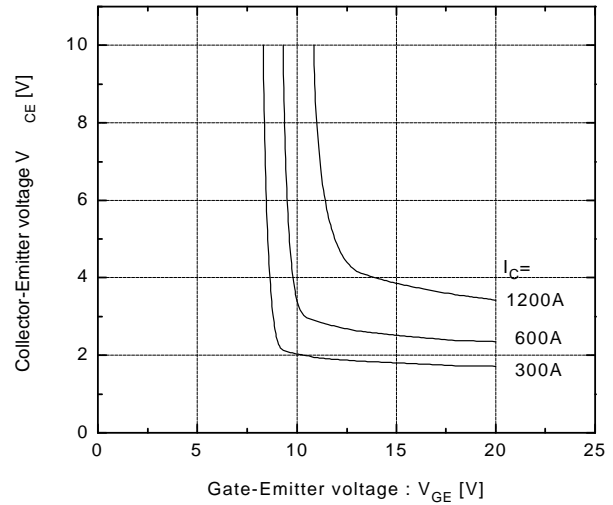
Collector current vs. Collector-Emittor voltage  
 $T_j=125^\circ\text{C}$



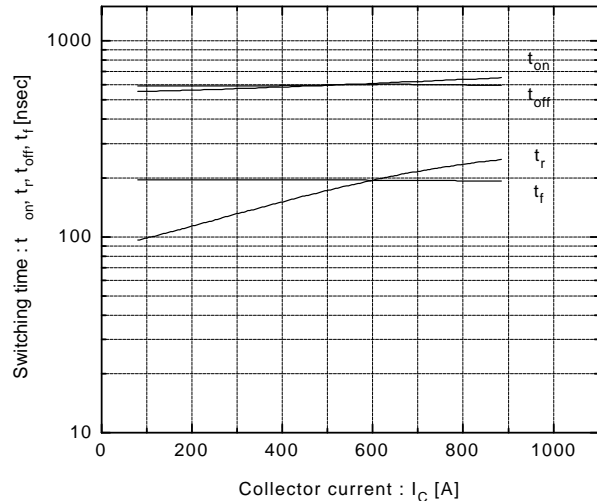
Collector-Emittor vs. Gate-Emittor voltage  
 $T_j=25^\circ\text{C}$



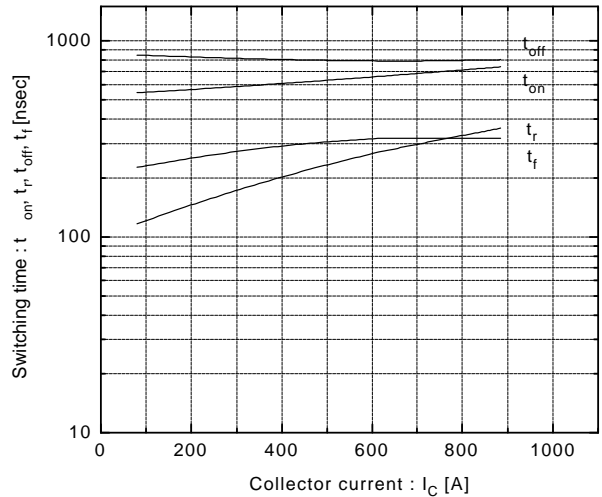
Collector-Emittor vs. Gate-Emittor voltage  
 $T_j=125^\circ\text{C}$



Switching time vs. Collector current  
 $V_{CC}=300\text{V}, R_G=2.7\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$



Switching time vs. Collector current  
 $V_{CC}=300\text{V}, R_G=2.7\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$



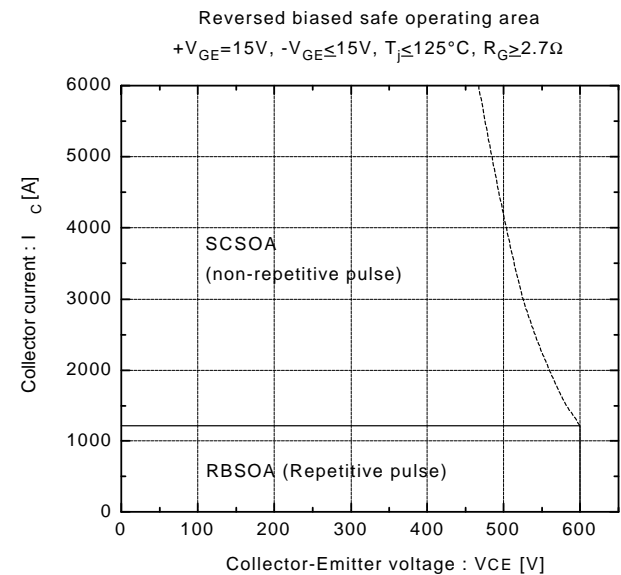
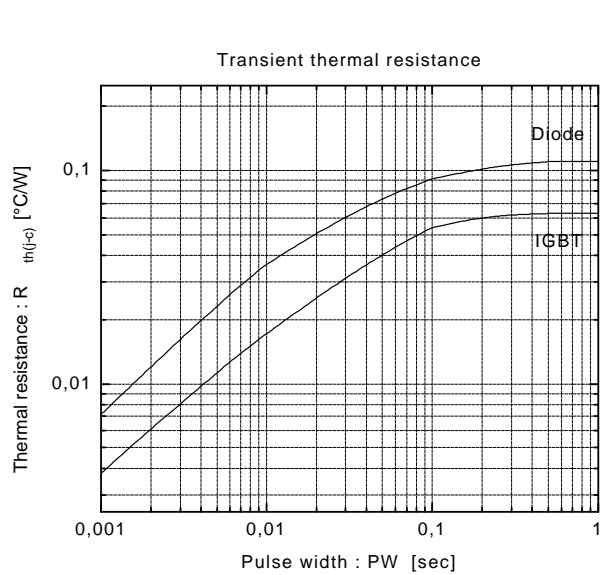
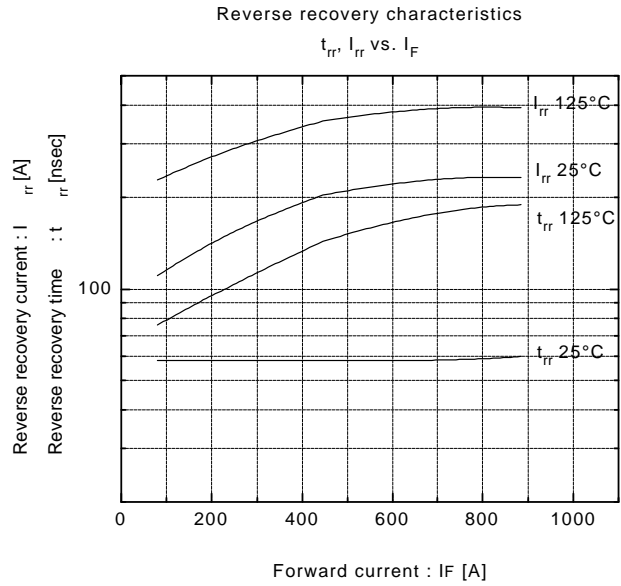
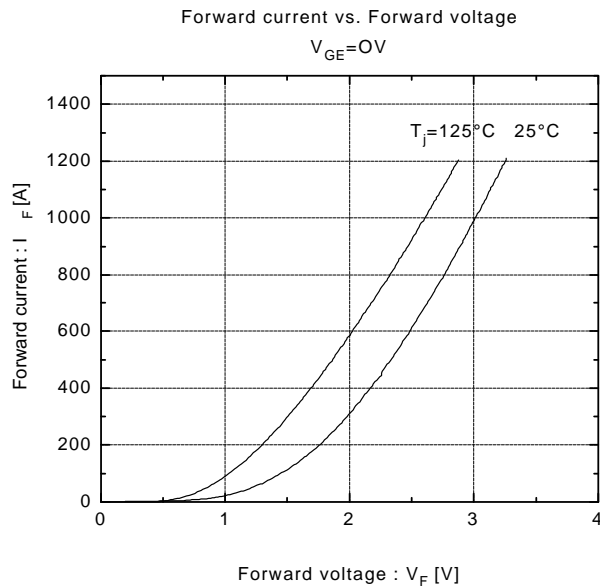
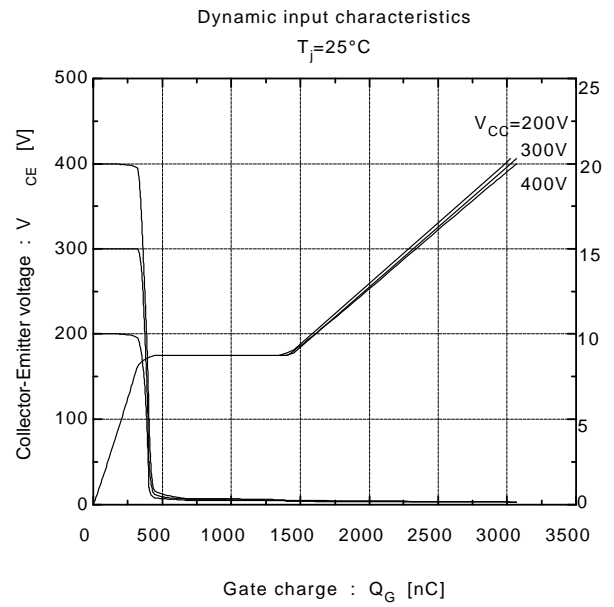
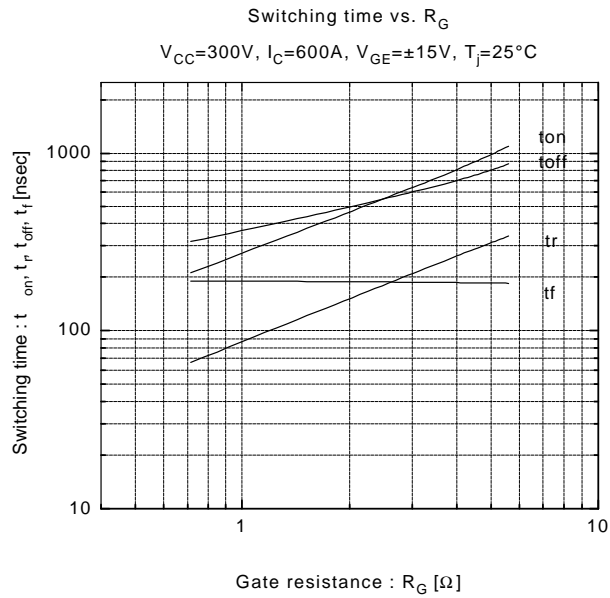
**FUJI**  
ELECTRIC

# 2MBI 600NT-060

2-Pack IGBT  
600 V  
600 A

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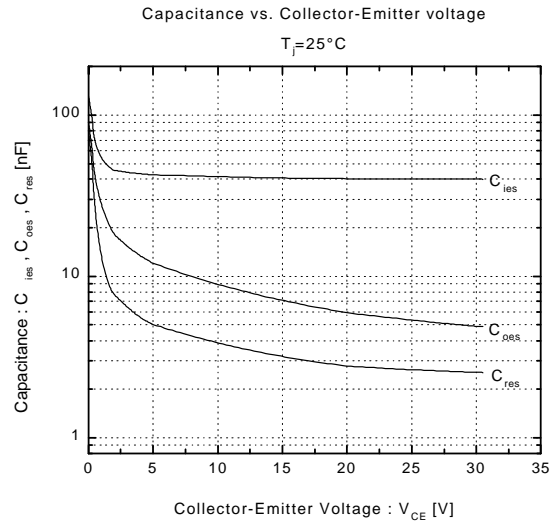
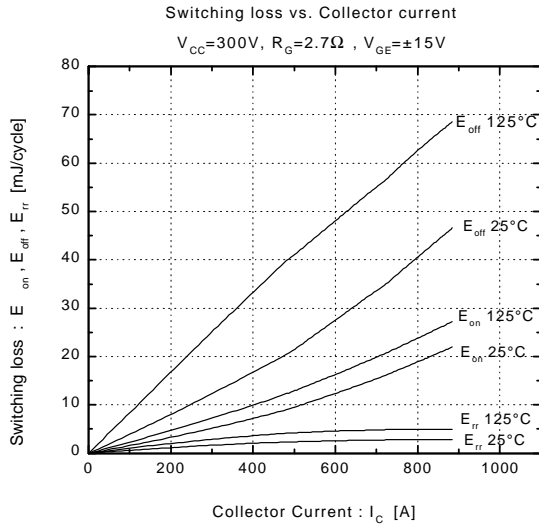
Gate-Emitter Voltage : V<sub>GE</sub> [V]



**FUJI**  
ELECTRIC

**2MBI 600NT-060**

**2-Pack IGBT**  
600 V  
600 A



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Specification is subject to change without notice

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